Jun Luo

List of Publications by Year
in descending order

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166	1,443	394421	501196
papers	citations	19 h-index	28 g-index

166	166	166	1205
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Narrow Sub-Fin Technique for Suppressing Parasitic-Channel Effect in Stacked Nanosheet Transistors. IEEE Journal of the Electron Devices Society, 2022, 10, 35-39.	2.1	9
2	Electrochemical surface reconstructed Pt_{x(x=2,3)}Si/PtSi/p-Si photocathodes for achieving high efficiency in photoelectrochemical H₂ generation. Journal of Materials Chemistry A, 2022, 10, 4952-4959.	10.3	6
3	Current controlled non-hysteresis magnetic switching in the absence of magnetic field. Applied Physics Letters, 2022, 120, 062402.	3.3	2
4	Temperature response of non-hysteresis magnetic switching by electrical current. Journal of Materials Science: Materials in Electronics, 2022, 33, 6681-6688.	2.2	1
5	Effects of Shallow Carbon and Deep N++ Layer on the Radiation Hardness of IHEP-IME LGAD Sensors. IEEE Transactions on Nuclear Science, 2022, 69, 1098-1103.	2.0	2
6	Mechanism Analysis of Ultralow Leakage and Abnormal Instability in InGaZnO Thin-Film Transistor Toward DRAM. IEEE Transactions on Electron Devices, 2022, 69, 2417-2422.	3.0	8
7	Field-Free Deterministic Writing of Spin-Orbit Torque Magnetic Tunneling Junction by Unipolar Current. IEEE Electron Device Letters, 2022, 43, 709-712.	3.9	4
8	Improving Driving Current with High-Efficiency Landing Pads Technique for Reduced Parasitic Resistance in Gate-All-Around Si Nanosheet Devices. ECS Journal of Solid State Science and Technology, 2022, 11, 035010.	1.8	4
9	4-Levels Vertically Stacked SiGe Channel Nanowires Gate-All-Around Transistor with Novel Channel Releasing and Source and Drain Silicide Process. Nanomaterials, 2022, 12, 889.	4.1	7
10	Experimental Investigation of Ultrathin Alâ„‚Oâ„‚ƒ Ex-Situ Interfacial Doping Strategy on Laminated HKMG Stacks via ALD. IEEE Transactions on Electron Devices, 2022, 69, 1964-1971.	3.0	3
11	Low-Temperature (â‰¤500 Â°C) Complementary Schottky Source/Drain FinFETs for 3D Sequential Integration. Nanomaterials, 2022, 12, 1218.	4.1	0
12	Insertion of Hafnium Interlayer to Improve the Thermal Stability of Ultrathin TiSi_x in TiSi_x/n⁺-Si Ohmic Contacts. IEEE Transactions on Electron Devices, 2022, 69, 3347-3352.	3.0	3
13	Investigation on Contacts Thermal Stability for 3D Sequential Integration. , 2022, , .		0
14	Ultralow Contact Resistivity on Ga-Doped Ge with Contact Co-Implantation of Ge and B. ECS Journal of Solid State Science and Technology, 2022, 11, 054002.	1.8	1
15	Vertical C-Shaped-Channel Nanosheet FETs Featured With Precise Control of Both Channel-Thickness and Gate-Length. IEEE Electron Device Letters, 2022, 43, 1183-1186.	3.9	9
16	Spin Logic Operated by Unipolar Voltage Inputs. IEEE Electron Device Letters, 2022, 43, 1239-1242.	3.9	3
17	Fabrication and selective wet etching of Si0.2Ge0.8/Ge multilayer for Si0.2Ge0.8 channel gate-all-around MOSFETs. Materials Science in Semiconductor Processing, 2021, 121, 105397.	4.0	8
18	Alleviation of negative-bias temperature instability in Si p-FinFETs with ALD W Gate-Filling Metal by Annealing Process optimization. IEEE Journal of the Electron Devices Society, 2021, , 1-1.	2.1	1

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19	Cryogenic Transport Characteristics of P-Type Gate-All-Around Silicon Nanowire MOSFETs. Nanomaterials, 2021, 11, 309.	4.1	12
20	A Fast DCIV Technique for Characterizing the Generation and Repassivation of Interface Traps Under DC/ AC NBTI Stress/Recovery Condition in Si p-FinFETs. , 2021, , .		0
21	Optimization of Structure and Electrical Characteristics for Four-Layer Vertically-Stacked Horizontal Gate-All-Around Si Nanosheets Devices. Nanomaterials, 2021, 11, 646.	4.1	30
22	Experimental Investigation of As Preamorphization Implant on Electrical Property of Ti-Based Silicide Contacts. IEEE Transactions on Electron Devices, 2021, 68, 1835-1840.	3.0	5
23	All-Linear Multistate Magnetic Switching Induced by Electrical Current. Physical Review Applied, 2021, 15, .	3.8	7
24	NiSi/pâº-Si(nâº-Si)/n-Si(p-Si) Diodes With Dopant Segregation (DS): p-n or Schottky Junctions?. IEEE Transactions on Electron Devices, 2021, 68, 2886-2891.	3.0	2
25	Four-Period Vertically Stacked SiGe/Si Channel FinFET Fabrication and Its Electrical Characteristics. Nanomaterials, 2021, 11, 1689.	4.1	10
26	Vertical Sandwich GAA FETs With Self-Aligned High-k Metal Gate Made by Quasi Atomic Layer Etching Process. IEEE Transactions on Electron Devices, 2021, 68, 2604-2610.	3.0	21
27	Thermal stability of SOT-MTJ thin films tuning by multiple interlayer couplings. Journal of Magnetism and Magnetic Materials, 2021, 529, 167823.	2.3	3
28	Novel Si/SiGe fin on insulator fabrication on bulk-Si substrate. Materials Research Express, 2021, 8, 075902.	1.6	1
29	Thermal stability issue of ultrathin Ti-based silicide for its application in prospective DRAM peripheral 3D FinFET transistors. Journal of Materials Science: Materials in Electronics, 2021, 32, 24107-24114.	2.2	4
30	Recovery Behavior of Interface Traps After Negative Bias Temperature Instability Stress in p-FinFETs Featuring Fast Trap Characterization Technique. IEEE Transactions on Electron Devices, 2021, 68, 4251-4258.	3.0	1
31	NiSi₂/p-Si Schottky Junction Photocathode with a High-Quality Epitaxial Interface for Efficient Hydrogen Evolution. ACS Applied Energy Materials, 2021, 4, 11574-11579.	5.1	4
32	A Novel Method to Reduce Specific Contact Resistivity of TiSi_x/n⁺-Si Contacts by Employing an In-Situ Steam Generation Oxidation Prior to Ti Silicidation. IEEE Electron Device Letters, 2021, 42, 958-961.	3.9	4
33	Comparison of DC/AC Hot Carrier Degradation between Short Channel Si Bulk and SiGe SOI p-FinFETs. , 2021, , .		0
34	Growth of SiGe layers in source and drain regions for 10Ânm node complementary metal-oxide semiconductor (CMOS). Journal of Materials Science: Materials in Electronics, 2020, 31, 26-33.	2.2	7
35	Design impact on the performance of Ge PIN photodetectors. Journal of Materials Science: Materials in Electronics, 2020, 31, 18-25.	2.2	31
36	Experimental investigation of fundamental film properties for Co1â^'xTix alloying films with different compositions (0â€‰â‰¤â€‰xâ‰¤1). Journal of Materials Science: Materials in Electronics, 2020, 31, 105-114.	2.2	0

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37	Vertical Sandwich Gate-All-Around Field-Effect Transistors With Self-Aligned High-k Metal Gates and Small Effective-Gate-Length Variation. IEEE Electron Device Letters, 2020, 41, 8-11.	3.9	46
38	Investigation on the formation technique of SiGe Fin for the high mobility channel FinFET device. Journal of Materials Science: Materials in Electronics, 2020, 31, 5854-5860.	2.2	2
39	Selective wet etching in fabricating SiGe nanowires with TMAH solution for gate-all-around MOSFETs. Journal of Materials Science: Materials in Electronics, 2020, 31, 22478-22486.	2.2	7
40	An Improved Dimensional Measurement Method of Staircase Patterns With Higher Precision in 3D NAND. IEEE Access, 2020, 8, 140054-140061.	4.2	3
41	Metal Silicidation in Conjunction with Dopant Segregation: A Promising Strategy for Fabricating High-Performance Silicon-Based Photoanodes. ACS Applied Materials & Interfaces, 2020, 12, 39092-39097.	8.0	10
42	Impact of Charges at Ferroelectric/Interlayer Interface on Depolarization Field of Ferroelectric FET With Metal/Ferroelectric/Interlayer/Si Gate-Stack. IEEE Transactions on Electron Devices, 2020, 67, 4500-4506.	3.0	20
43	Investigation of Ultrathin Ni Germanosilicide for Advanced pMOS Contact Metallization. IEEE Transactions on Electron Devices, 2020, 67, 5039-5044.	3.0	2
44	Understanding Frequency Dependence of Trap Generation Under AC Negative Bias Temperature Instability Stress in Si p-FinFETs. IEEE Electron Device Letters, 2020, 41, 965-968.	3.9	11
45	Insights Into the Effect of TiN Thickness Scaling on DC and AC NBTI Characteristics in Replacement Metal Gate pMOSFETs. IEEE Transactions on Device and Materials Reliability, 2020, 20, 498-505.	2.0	3
46	Influence of TaN films deposited using different N2 flow rates on the properties of Ta and Cu films in advanced 3D NAND memory. Materials Science in Semiconductor Processing, 2020, 115, 105120.	4.0	4
47	Specific Contact Resistivity Improvement by As Preamorphization Implantation for Ti-Based Ohmic Contacts on n+-Si. IEEE Transactions on Electron Devices, 2020, 67, 1726-1729.	3.0	7
48	Impact of Ge pre-amorphization implantation on Co/Co-Ti/n⁺-Si contacts in advanced Co interconnects. Japanese Journal of Applied Physics, 2020, 59, SLLB01.	1.5	2
49	Role of Carbon Pre-Germanidation Implantation on Enhancing the Thermal Stability of NiGe Films Below 10 nm Thickness. ECS Journal of Solid State Science and Technology, 2020, 9, 054006.	1.8	4
50	High thermoelectric power factor of p-type amorphous silicon thin films dispersed with ultrafine silicon nanocrystals. Journal of Applied Physics, 2020, 127, .	2.5	10
51	Fabrication technique of the Si_{0.5}Ge_{0.5} Fin for the high mobility channel FinFET device. Semiconductor Science and Technology, 2020, 35, 045015.	2.0	12
52	Effects of Ni Film Thickness on the Properties of Ni-Based Silicides Formed on Both Highly Doped n- and p-Si Substrate. ECS Journal of Solid State Science and Technology, 2020, 9, 034001.	1.8	2
53	Comparative study on NBTI kinetics in Si p-FinFETs with B2H6-based and SiH4-based atomic layer deposition tungsten (ALD W) filling metal. Microelectronics Reliability, 2020, 107, 113627.	1.7	5
54	Study of Silicon Nitride Inner Spacer Formation in Process of Gate-all-around Nano-Transistors. Nanomaterials, 2020, 10, 793.	4.1	19

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55	Investigation of Barrier Property of Amorphous Coâ€“Ti Layer as Single Barrier/Liner in Local Co Interconnects. IEEE Transactions on Electron Devices, 2020, 67, 2076-2081.	3.0	7
56	Investigation on thermal stability of Si_{0.7}Ge_{0.3}/Si stacked multilayer for gate-all-around MOSFETS. Semiconductor Science and Technology, 2020, 35, 115008.	2.0	10
57	Key Process Technologies for Stacked Double Si_{0.7}Ge_{0.3} Channel Nanowires Fabrication. ECS Journal of Solid State Science and Technology, 2020, 9, 064009.	1.8	6
58	An Improved Rosin Transfer Process for the Reduction of Residue Particles for Graphene. Nanoscale Research Letters, 2020, 15, 85.	5.7	6
59	Spin Logic Devices via Electric Field Controlled Magnetization Reversal by Spin-Orbit Torque. IEEE Electron Device Letters, 2019, 40, 1554-1557.	3.9	69
60	Titanium-based ohmic contacts in advanced CMOS technology. Journal Physics D: Applied Physics, 2019, 52, 503001.	2.8	20
61	Effect of interfacial Ni between graphene and Pt/Au on reducing specific contact resistivity. Japanese Journal of Applied Physics, 2019, 58, SHHD02.	1.5	0
62	Process optimization of the Si_{0.7}Ge_{0.3} Fin Formation for the STI first scheme. Semiconductor Science and Technology, 2019, 34, 125008.	2.0	10
63	Impacts of Ge Preamorphization Implantation and Si Capping on the Specific Contact Resistivity of Ni(Pt)SiGe/p⁺-SiGe Contacts. IEEE Transactions on Electron Devices, 2019, 66, 4331-4336.	3.0	2
64	Influence of Polysilicon Deposition Conditions on Advanced 3D NAND. ECS Journal of Solid State Science and Technology, 2019, 8, Q207-Q210.	1.8	1
65	Impact of Post High-Îº Deposition Anneal (PDA) and Post High-Îº Capping Anneal (PCA) on the xBTI Performance in HfO₂-Based FinFETs. ECS Journal of Solid State Science and Technology, 2019, 8, P30-P34.	1.8	3
66	Exploration of the impact of interface states density on the specific contact resistivity in TiSi_x/n⁺-Si Ohmic contacts through high-low frequency method. Japanese Journal of Applied Physics, 2019, 58, SHHD01.	1.5	2
67	Co-sputtering Coâ€“Ti alloy as a single barrier/liner for Co interconnects and thermal stability enhancement using TiN metal capping. Journal of Materials Science: Materials in Electronics, 2019, 30, 10579-10588.	2.2	5
68	Investigation of NiGe Films Formed on Both n⁺- and p⁺-Ge with P and B Ion Implantation before Germanidation. ECS Journal of Solid State Science and Technology, 2019, 8, P271-P276.	1.8	0
69	High crystal quality strained Si0.5Ge0.5 layer with a thickness of up to 50â€¯nm grown on the three-layer SiGe strain relaxed buffer. Materials Science in Semiconductor Processing, 2019, 99, 159-164.	4.0	8
70	Comparison of NBTI kinetics in RMG Si p-FinFETs featuring Atomic Layer Deposition Tungsten (ALD W) Filling Metal Using B2H6 and SiH4 Precursors. , 2019, , .		0
71	A Comparative Study of TiN Thickness Scaling Impact on DC and AC NBTI Kinetics in Replacement Metal Gate pMOSFETs. , 2019, , .		3
72	Effects of Different Ion Irradiation on the Contact Resistance of Pd/Graphene Contacts. Materials, 2019, 12, 3928.	2.9	7

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73	Effects of Ar Plasma Treatment on the Properties of TaN/Ta Barrier for Copper Interconnects in Advanced 3D NAND Memory. ECS Journal of Solid State Science and Technology, 2019, 8, P764-P767.	1.8	1
74	Optimization of Etch Process for Ultra-Narrow Via in 3D NAND Flash Memory by DOE Method. ECS Journal of Solid State Science and Technology, 2019, 8, P775-P786.	1.8	0
75	Edge-Contact Formed by Oxygen Plasma and Rapid Thermal Annealing to Improve Metal-Graphene Contact Resistance. ECS Journal of Solid State Science and Technology, 2018, 7, M11-M15.	1.8	4
76	Improved Ti germanosilicidation by Ge pre-amorphization implantation (PAI) for advanced contact technologies. Microelectronic Engineering, 2018, 201, 1-5.	2.4	5
77	Impact of Ge Preamorphization Implantation on Both the Formation of Ultrathin TiSi_{<italic>x</italic>} and the Specific Contact Resistivity in TiSi_{<italic>x</italic>}/n-Si Contacts. IEEE Transactions on Electron Devices, 2018, 65, 4490-4498.	3.0	17
78	Enhancing the thermal stability of NiGe by prior-germanidation fluorine implantation into Ge substrate. Japanese Journal of Applied Physics, 2018, 57, 07MA03.	1.5	3
79	On the manifestation of Ge pre-amorphization implantation (PAI) impact on both the formation of ultrathin TiSi<inf>x</inf> and the specific contact resistivity in TiSi<inf>x</inf>/n-Si contacts for sub-16/14 nm nodes and beyond. , 2018, , .		0
80	Impact of Ge pre-amorphization implantation on forming ultrathin TiGe x on both n- and p-Ge substrate. Japanese Journal of Applied Physics, 2018, 57, 07MA02.	1.5	2
81	Advanced contact technology. , 2018, , 157-213.		0
82	Switching of Exchange-Coupled Perpendicularly Magnetized Layers Under Spinâ€“Orbit Torque. IEEE Transactions on Magnetics, 2018, 54, 1-4.	2.1	0
83	Tuning of Schottky Barrier Height at NiSi/Si Contact by Combining Dual Implantation of Boron and Aluminum and Microwave Annealing. Materials, 2018, 11, 471.	2.9	0
84	Study on NBTI improvement of HfO<inf>2</inf>-based 14 nm P-type FinFET with post high-k deposition thermal treatment. , 2018, , .		0
85	A Study of High-Low Frequency Charge Pumping Method on Evaluating Interface Traps in Bulk FinFETs. ECS Journal of Solid State Science and Technology, 2018, 7, Q164-Q168.	1.8	0
86	Two methods of tuning threshold voltage of bulk FinFETs with replacement high-k metal-gate stacks. Solid-State Electronics, 2017, 129, 52-60.	1.4	9
87	Hot Implantations of P into Ge: Impact on the Diffusion Profile. ECS Journal of Solid State Science and Technology, 2017, 6, P73-P77.	1.8	4
88	Optimization of Selective Growth of SiGe for Source/Drain in 14nm and Beyond Nodes FinFETs. International Journal of High Speed Electronics and Systems, 2017, 26, 1740003.	0.7	3
89	Integration of Highly Strained SiGe in Source and Drain with HK and MG for 22Ânm Bulk PMOS Transistors. Nanoscale Research Letters, 2017, 12, 123.	5.7	22
90	Understanding the microwave annealing of silicon. AIP Advances, 2017, 7, .	1.3	22

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91	Physically Based Evaluation of Effect of Buried Oxide on Surface Roughness Scattering Limited Hole Mobility in Ultrathin GeOI MOSFETs. IEEE Transactions on Electron Devices, 2017, 64, 2611-2616.	3.0	9
92	Low frequency noise characterization of 22nm PMOS featuring with filling W gate using different precursors. , 2017, , .		0
93	Optimization of Selective Growth of SiGe for Source/Drain in 14nm and Beyond Nodes FinFETs. Selected Topics in Electornics and Systems, 2017, , 99-107.	0.2	1
94	On the Manifestation of Ge Pre-Amorphization Implantation (PAI) in Forming Ultrathin TiSi_xfor Ti Direct Contact on Si in Sub-16/14 nm Complementary Metal-Oxide-Semiconductor (CMOS) Technology Nodes. ECS Journal of Solid State Science and Technology, 2017, 6, P660-P664.	1.8	10
95	pMOSFETs Featuring ALD W Filling Metal Using SiH4 and B2H6 Precursors in 22 nm Node CMOS Technology. Nanoscale Research Letters, 2017, 12, 306.	5.7	13
96	A Modified Scheme to Reduce the Specific Contact Resistivity of NiSi/Si Contacts by Means of Dopant Segregation Technique. ECS Journal of Solid State Science and Technology, 2017, 6, P904-P908.	1.8	3
97	FinFETs on insulator with silicided source/drain. , 2017, , .		1
98	Impact of DSOI back-gate biasing on circuit conducted emission. , 2017, , .		0
99	Enhanced End-Contacts by Helium Ion Bombardment to Improve Graphene-Metal Contacts. Nanomaterials, 2016, 6, 158.	4.1	6
100	Schottky Barrier Height Tuning via the Dopant Segregation Technique through Low-Temperature Microwave Annealing. Materials, 2016, 9, 315.	2.9	2
101	(Invited) On the Manipulation of Phosphorus Diffusion as Well as the Reduction of Specific Contact Resistivity in Ge by Carbon Co-Doping. ECS Transactions, 2016, 75, 219-226.	0.5	0
102	FOI FinFET with ultra-low parasitic resistance enabled by fully metallic source and drain formation on isolated bulk-fin. , 2016, , .		27
103	Reduction of NiGe/n- and p-Ge Specific Contact Resistivity by Enhanced Dopant Segregation in the Presence of Carbon During Nickel Germanidation. IEEE Transactions on Electron Devices, 2016, 63, 4546-4549.	3.0	13
104	Electromagnetic susceptibility characterization of double SOI device. Microelectronics Reliability, 2016, 64, 168-171.	1.7	12
105	Impact of pattern dependency of SiGe layers grown selectively in source/drain on the performance of 14nm node FinFETs. Solid-State Electronics, 2016, 124, 10-15.	1.4	18
106	Integration of Selective Epitaxial Growth of SiGe/Ge Layers in 14nm Node FinFETs. ECS Transactions, 2016, 75, 273-279.	0.5	4
107	Defect engineering for shallow nâ€type junctions in germanium: Facts and fiction. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2799-2808.	1.8	18
108	Study of SiGe selective epitaxial process integration with high-k and metal gate for 16/14nm nodes FinFET technology. Microelectronic Engineering, 2016, 163, 49-54.	2.4	18

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109	Junction Control by Carbon and Phosphorus Co-Implantation in Pre-Amorphized Germanium. ECS Journal of Solid State Science and Technology, 2016, 5, P315-P319.	1.8	7
110	Random telegraph noise: The key to single defect studies in nano-devices. Thin Solid Films, 2016, 613, 2-5.	1.8	8
111	Impact of the Effective Work Function Gate Metal on the Low-Frequency Noise of Gate-All-Around Silicon-on-Insulator NWFETs. IEEE Electron Device Letters, 2016, 37, 363-365.	3.9	19
112	Evaluation of PMMA Residues as a Function of Baking Temperature and a Graphene Heat-Free-Transfer Process to Reduce Them. ECS Journal of Solid State Science and Technology, 2016, 5, P138-P141.	1.8	7
113	Atomic layer deposition assisted pattern transfer technology for ultra-thin block copolymer films. Thin Solid Films, 2016, 613, 32-37.	1.8	5
114	(Invited) The Assessment of Border Traps in High-Mobility Channel Materials. ECS Transactions, 2015, 69, 205-217.	0.5	0
115	Silicon-film-related random telegraph noise in UTBOX silicon-on-insulator nMOSFETs. Journal of Semiconductors, 2015, 36, 094005.	3.7	2
116	Investigation of TaN as the wet etch stop layer for HKMG-last integration in the 22Ânm and beyond nodes CMOS technology. Vacuum, 2015, 119, 185-188.	3.5	3
117	Distinction between silicon and oxide traps using single-trap spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 512-517.	1.8	15
118	Effect of hydrogen carrier gas on AlN and AlGaN growth in AMEC Prismo D-Blue Â® MOCVD platform. Journal of Crystal Growth, 2015, 419, 52-56.	1.5	23
119	Effects of Carbon Pre-Germanidation Implantation on the Thermal Stability of NiGe and Dopant Segregation on Both n- and p-Type Ge Substrate. ECS Journal of Solid State Science and Technology, 2015, 4, P119-P123.	1.8	11
120	Electrical detection of single particle in cylindrical solid-state nanopores. , 2015, , .		0
121	Low-frequency noise study of Ge p-MOSFETs with HfO<inf>2</inf>/Al<inf>2</inf>O<inf>3</inf>/GeO<inf>x</inf> gate stack. , 2015, , .		1
122	Impact of pattern dependency of SiGe layers grown selectively in source/drain on the performance of 22nm node pMOSFETs. Solid-State Electronics, 2015, 114, 43-48.	1.4	14
123	Application of ALD W films as gate filling metal in 22nm HKMG-last integration: Evaluation and improvement of the adhesion in CMP process. Microelectronic Engineering, 2015, 137, 43-46.	2.4	14
124	Improvement of the Thermal Stability of Nickel Stanogermanide by Carbon Pre-Stanogermanidation Implant into GeSn Substrate. ECS Journal of Solid State Science and Technology, 2015, 4, P67-P70.	1.8	13
125	Towards singleâ€trap spectroscopy: Generationâ€recombination noise in UTBOX SOI nMOSFETs. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 292-298.	0.8	15
126	FinFETs using reverse substrate layer with improved gate capacitance characteristics for subthreshold application. Solid-State Electronics, 2015, 104, 116-121.	1.4	2

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127	Simulation analysis of nanopore performance in single-nanoparticle detection. , 2015, , .		2
128	Low-Frequency Noise Characterization of GeO_{<italic>x</italic>} Passivated Germanium MOSFETs. IEEE Transactions on Electron Devices, 2015, 62, 2078-2083.	3.0	17
129	Effects of defects and thermal treatment on the properties of graphene. Vacuum, 2015, 116, 90-95.	3.5	30
130	Device parameter optimization for sub-20 nm node HK/MG-last bulk FinFETs. Journal of Semiconductors, 2015, 36, 044007.	3.7	5
131	Simulation and characterization of stress in FinFETs using novel LKMC and nanobeam diffraction methods. Journal of Semiconductors, 2015, 36, 086001.	3.7	2
132	Integration of highly-strained SiGe materials in 14 nm and beyond nodes FinFET technology. Solid-State Electronics, 2015, 103, 222-228.	1.4	45
133	Effects of carbon pre-germanidation implant into Ge on the thermal stability of NiGe films. Microelectronic Engineering, 2015, 133, 6-10.	2.4	6
134	Two-terminal vertical memory cell for cross-point static random access memory applications. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 021205.	1.2	3
135	Co-implantation with microwave annealing for phosphorous shallow-junction formation in Germanium. , 2014, , .		1
136	Study of ΔID/ID of a single charge trap in utbox silicon films. , 2014, , .		0
137	Study of Random Telegraph Noise in UTBOX Silicon-on-Insulator nMOSFETs. ECS Transactions, 2014, 60, 109-114.	0.5	3
138	Application of Atomic Layer Deposition Tungsten (ALD W) as Gate Filling Metal for 22 nm and Beyond Nodes CMOS Technology. ECS Journal of Solid State Science and Technology, 2014, 3, P82-P85.	1.8	32
139	Innovatively composite hard mask to feature sub-30nm gate patterning. Microelectronic Engineering, 2014, 127, 7-13.	2.4	11
140	Mechanism of TMAl pre-seeding in AlN epitaxy on Si (111) substrate. Vacuum, 2014, 101, 184-188.	3.5	26
141	Mitigation of Reverse Short-Channel Effect With Multilayer TiN/Ti/TiN Metal Gates in Gate Last PMOSFETs. IEEE Electron Device Letters, 2014, 35, 811-813.	3.9	3
142	Self-assembling morphologies of symmetrical PS-b-PMMA in different sized confining grooves. RSC Advances, 2014, 4, 50393-50400.	3.6	9
143	Effects of carbon pre-silicidation implant into Si substrate on NiSi. Microelectronic Engineering, 2014, 120, 178-181.	2.4	14
144	Variation of Schottky barrier height induced by dopant segregation monitored by contact resistivity measurements. Microelectronic Engineering, 2014, 120, 174-177.	2.4	7

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145	A modified scheme to tune the Schottky Barrier Height of NiSi by means of dopant segregation technique. Vacuum, 2014, 99, 225-227.	3.5	7
146	Systematic comparison between a new lattice kinetic Monte Carlo method and conventional polyhedron method for stress simulation in FinFETs. , 2014, , .		0
147	Ultra-shallow junctions formed using microwave annealing. Applied Physics Letters, 2013, 102, .	3.3	30
148	Optimization of SiGe selective epitaxy for source/drain engineering in 22â€‰nm node complementary metal-oxide semiconductor (CMOS). Journal of Applied Physics, 2013, 114, 123511.	2.5	37
149	Application of Atomic Layer Deposition Tungsten (ALD W) as Gate Filling Metal for 22 nm and Beyond Nodes CMOS Technology. ECS Transactions, 2013, 58, 317-324.	0.5	9
150	A New Solution to the Ni-fill issue for Silicide-last Process. Materials Research Society Symposia Proceedings, 2013, 1559, 1.	0.1	0
151	Evaluation of TaN as the Wet Etch Stop Layer during the 22nm HKMG Gate Last CMOS Integrations. ECS Transactions, 2013, 58, 111-118.	0.5	1
152	A more CMOS process compatible scheme to tune the Schottky Barrier Height of NiSi to electrons by means of dopant segregation (DS) technique. , 2012, , .		0
153	Vertically stacked individually tunable nanowire field effect transistors for low power operation with ultrahigh radio frequency linearity. Applied Physics Letters, 2012, 101, 093509.	3.3	4
154	Extensive Raman spectroscopic investigation of ultrathin Co1â^'xNixSi2 films grown on Si(100). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, 041511.	2.1	3
155	Gap fill capability of Ni PVD based on silicide-last process. , 2012, , .		0
156	Performance Breakthrough in Gate-All-Around Nanowire n- and p-Type MOSFETs Fabricated on Bulk Silicon Substrate. IEEE Transactions on Electron Devices, 2012, 59, 1885-1890.	3.0	16
157	Thermal Stability and Dopant Segregation for Schottky Diodes With Ultrathin Epitaxial $hbox{NiSi}_{2 - y}$. IEEE Electron Device Letters, 2011, 32, 1029-1031.	3.9	10
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